

### **isc Silicon NPN Power Transistor**

## 2SC3871

#### **DESCRIPTION**

- · Collector-Base Breakdown Voltage-
  - : V<sub>(BR)CBO</sub>= 500V(Min.)
- · Low Collector Saturation Voltage
- · Wide Area of Safe Operation
- · High Speed Switching
- · Minimum Lot-to-Lot variations for robust device performance and reliable operation

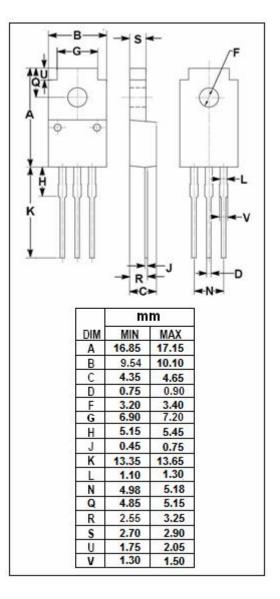
# PIN 1. BASE 2.COLLECTOR 3. BMITTER TO-220Fa package

#### **APPLICATIONS**

· Designed for high speed switching applications.

ABSOLUTE MAXIMUM RATINGS (Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>СВО</sub>	Collector-Base Voltage	500	V	
V <sub>CES</sub>	Collector-Emitter Voltage	500	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	400	V	
V <sub>EBO</sub>	Emitter-Base Voltage	7	V	
Ic	Collector Current-Continuous	10	Α	
Ісм	Collector Current-Peak	20	А	
I <sub>B</sub>	Base Current-Continuous	5	А	
P <sub>C</sub>	Collector Power Dissipation @T <sub>a</sub> =25℃	2		
	Collector Power Dissipation @T <sub>C</sub> =25°C	45	W	
T <sub>j</sub>	Junction Temperature	150	$^{\circ}$ C	
T <sub>stg</sub>	Storage Temperature Range	-55~150	$^{\circ}\mathbb{C}$	





#### isc Silicon NPN Power Transistor

2SC3871

#### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

Tc=25 C unless otherwise specified									
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT			
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA; I <sub>B</sub> = 0	400			V			
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 1A			1.0	V			
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 1A			1.5	V			
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 500V; I <sub>E</sub> = 0			100	μА			
I <sub>ЕВО</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			100	μА			
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.1A; V <sub>CE</sub> = 5V	15						
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 5A; V <sub>CE</sub> = 5V	8						
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 10V	15			MHz			
Switching T	îmes								
ton	Turn-on Time				0.7	μs			
ts	Storage Time	I <sub>C</sub> = 5A; I <sub>B1</sub> = 1A; I <sub>B2</sub> = -2A; V <sub>CC</sub> = 150V			2.0	μs			
t <sub>f</sub>	Fall Time				0.3	μS			

#### **NOTICE:**

ISC reserves the rights to make changes of the content herein the datasheet at any time without notification. The information contained herein is presented only as a guide for the applications of our products.

ISC products are intended for usage in general electronic equipment. The products are not designed for use in equipment which require specialized quality and/or reliability, or in equipment which could have applications in hazardous environments, aerospace industry, or medical field. Please contact us if you intend our products to be used in these special applications.

ISC makes no warranty or guarantee regarding the suitability of its products for any particular purpose, nor does ISC assume any liability arising from the application or use of any products, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.

isc website: www.iscsemi.com